

2SA698

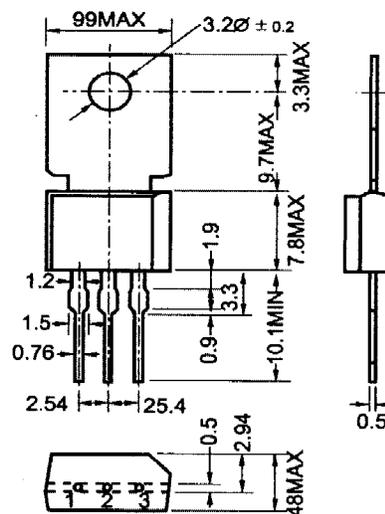
Silicon PNP Transistors

◆ Features

□ With TO-202 package

◆ Absolute Maximum Ratings $T_c=25^\circ\text{C}$ □

SYMBOL	PARAMETER	RATING	UNIT
V_{CB0}	Collector to base voltage	130	V
V_{CE0}	Collector to emitter voltage	130	V
V_{EB0}	Emitter to base voltage	5.0	V
I_B	Base current		
I_C	Collector current	0.8	A
P_C	Collector power dissipation	7	W
T_j	Junction temperature	150	□
T_{stg}	Storage temperature	-55~150	□



TO-202

◆ Electrical Characteristics $T_c=25^\circ\text{C}$ □

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
I_{CB0}	Collector-base cut-off current	$V_{CB}=120\text{V}; I_E=0$			1	μA
I_{EB0}	Emitter-base cut-off current	$V_{EB}=5\text{V}; I_C=0$			100	μA
I_{CE0}	Collector-emitter cut-off current	$V_{CE}=120\text{V}; I_E=0$			100	μA
V_{CB0}	Collector-base breakdown voltage	$I_C=1\text{mA}; I_E=0$	130			V
V_{CE0}	Collector-emitter voltage	$I_C=10\text{mA}; I_B=0$	130			V
V_{EB0}	Emitter-base breakdown voltage					
$V_{CE(sat-1)}$	Collector-emitter saturation voltages	$I_C=0.5\text{A}; I_B=0.05\text{A}$			1.0	V
$V_{CE(sat-2)}$	Collector-emitter saturation voltages					
h_{FE-1}	Forward current transfer ratio					
h_{FE-2}	Forward current transfer ratio	$I_C=0.2\text{A}; V_{CE}=5\text{V}$	60		200	
$V_{BE(sat)1}$	Base-emitter saturation voltages					
$V_{BE(sat)2}$	Base-emitter saturation voltages					
$V_{BE(sat)3}$	Base-emitter saturation voltages					
f_T	Transition frequency at $f=1\text{MHz}$					

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

